MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

# **TPN13008NH**

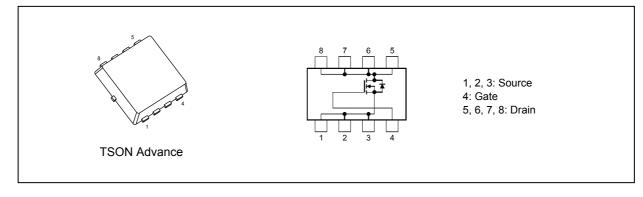
#### 1. Applications

- DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

#### 2. Features

- (1) Small, thin package
- (2) High-speed switching
- (3) Small gate charge:  $Q_{SW} = 6.7 \text{ nC}$  (typ.)
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 10.8 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 10 \text{ V})$
- (5) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 80 \ V)$
- (6) Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.2 mA)

#### 3. Packaging and Internal Circuit



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#### 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristi	cs		Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	80	V
Gate-source voltage			V <sub>GSS</sub>	±20	V
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	ID	40	A
Drain current (DC)	(T <sub>c</sub> = 25 °C)	(Note 1)	I <sub>D</sub>	18	
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I <sub>DP</sub>	98	A
Power dissipation	(T <sub>c</sub> = 25 °C)		PD	42	W
Power dissipation	(t = 10 s)	(Note 3)	PD	1.9	W
Power dissipation	(t = 10 s)	(Note 4)	PD	0.7	W
Single-pulse avalanche energy		(Note 5)	E <sub>AS</sub>	114	mJ
Avalanche current			I <sub>AR</sub>	18	A
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	(T <sub>c</sub> = 25 °C)		R <sub>th(ch-c)</sub>	2.97	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R <sub>th(ch-a)</sub>	65.7	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R <sub>th(ch-a)</sub>	178	

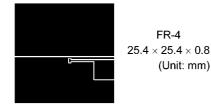
Note 1: Ensure that the channel temperature does not exceed 150 °C.

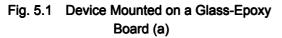
Note 2: Limited by silicon chip capability.

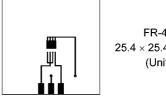
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5:  $V_{DD}$  = 60 V,  $T_{ch}$  = 25 °C (initial), L = 0.3 mH,  $R_G$  = 1.0  $\Omega$ ,  $I_{AR}$  = 18 A







FR-4  $25.4\times25.4\times0.8$ (Unit: mm)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

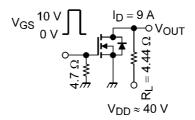
### 6. Electrical Characteristics

### 6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_	_	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V	_		10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	80	—	—	V
	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	60	_	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.2 mA	2.0	—	4.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 9 A		10.8	13.3	mΩ

### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	1230	1600	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	20	50	
Output capacitance	C <sub>oss</sub>		_	290	_	
Gate resistance	rg	—	_	0.9	1.4	Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1	_	4.5	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	14	_	
Switching time (fall time)	t <sub>f</sub>		_	5.0	_	
Switching time (turn-off time)	t <sub>off</sub>		_	18	_	



 $\label{eq:buty} \begin{array}{l} Duty \leq 1\%, \ t_w = 10 \ \mu s \end{array}$  Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

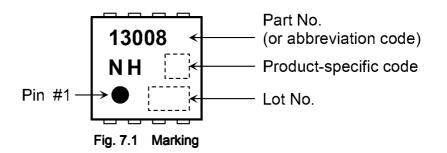
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 40$ V, $V_{GS}$ = 10 V, $I_D$ = 18 A	_	18	—	nC
Gate-source charge 1	Q <sub>gs1</sub>			6.5	_	
Gate-drain charge	Q <sub>gd</sub>		_	4.0	_	
Gate switch charge	Q <sub>SW</sub>		_	6.7	_	

### 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

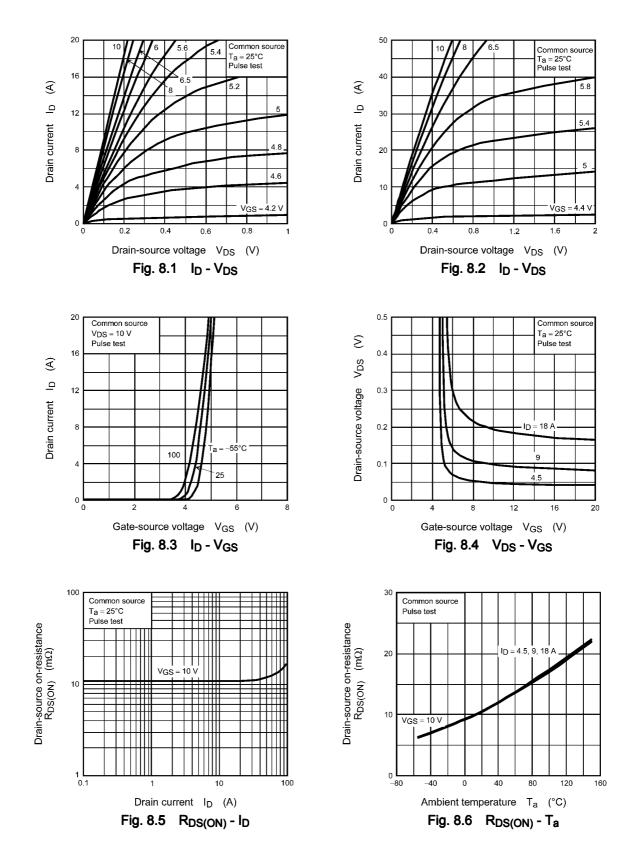
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 6)	I <sub>DRP</sub>	—	_	—	98	А
Diode forward voltage		$V_{DSF}$	I <sub>DR</sub> = 18 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V

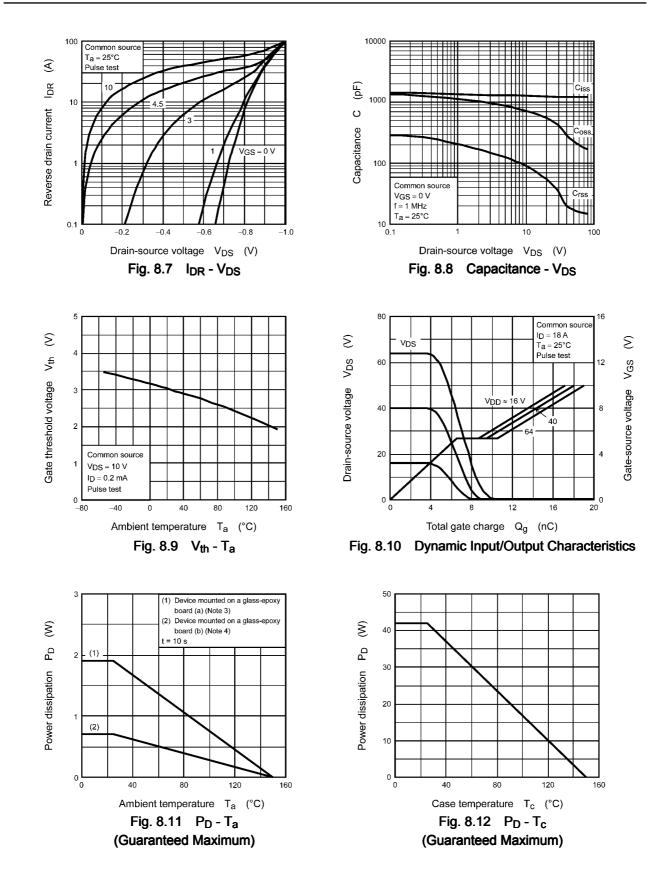
Note 6: Ensure that the channel temperature does not exceed 150  $^\circ\text{C}.$ 

### 7. Marking



#### 8. Characteristics Curves (Note)





1000

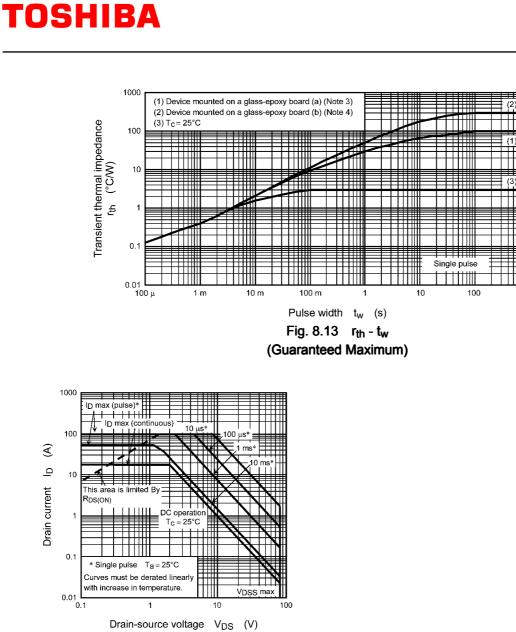


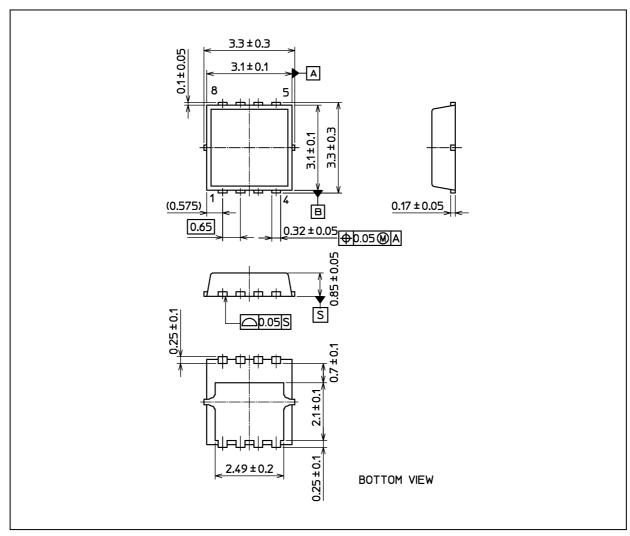
Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## TPN13008NH

### Package Dimensions

Unit: mm



Weight: 0.029 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance

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